

## Examples for Searching with the ET Field

1. Chemical formulas and nuclear reactions as well as fragments are analysed. The program distinguishes between upper and lower cases. E.g. the analysis of GaP results in the following index terms:

GaP; Ga\*P; Ga cp; P cp; cp (cp = compounds),

while the word 'gap' (like in 'energy gap') is not analysed.

(Upper and lower case characters are retained in DISPLAY, but cannot be used in SEARCH.)

```
=> S GAP/ET
L1      6741 GAP/ET

=> D TRIAL

L1 ANSWER 1 OF 6741 INSPEC COPYRIGHT 2000 FIZ KARLSRUHE
TI Crystal characterization of GaP epilayer grown on GaAs by atmospheric
   pressure metalorganic vapor phase epitaxy.
CC A6855 Thin film growth, structure, and epitaxy; A7830G Infrared and Raman spectra
   in inorganic crystals; A7865K Optical properties of III-V and II-VI semi-conductors
   (thin films/low-dimensional structures); A7920N Atom-, molecule-, and ion-surface
   impact and interactions; A6480E Stoichiometry and homogeneity; A8115H Chemical
   vapour deposition; B2520D II-VI and III-V semi-conductors; B0520F Chemical vapour
   deposition
CT GALLIUM COMPOUNDS; III-V SEMI CONDUCTORS; INTERNAL STRESSES; MOCVD; RAMAN
   SPECTRA; RUTHERFORD BACKSCATTERING; SEMI CONDUCTOR EPITAXIAL LAYERS;
   SEMI CONDUCTOR GROWTH; STOICHIOMETRY; VAPOUR PHASE EPITAXIAL GROWTH; X-RAY
   DIFFRACTION
ST epilayer; crystal structure; metalorganic vapor phase epitaxy; X-ray diffraction;
   backscattering spectrometry; Raman scattering; morphology; growth temperature;
   temperature dependence; V/III ratio; biaxial stress model; residual strain; 800 C;
   GaP; GaAs
CHI GaP bin, Ga bin, P bin; GaAs sur, As sur, Ga sur, GaAs bin, As bin, Ga bin
PHP temperature 1.07E+03 K
ET Ga*P; ***GaP*** ; Ga cp; cp; P cp; As*Ga; As sy 2; sy 2; Ga sy 2; GaAs;
   As cp; C; V; Ga; P; As
```

```
=> S GAP NOT GAP/ET
      111146 GAP
      6741 GAP/ET
L2      104447 GAP NOT GAP/ET

=> D 1792 HIT ET

L2 ANSWER 1792 OF 104447 INSPEC COPYRIGHT 2000 IEE
AB In the context of extended t-J models, with intersite Coulomb interactions of the
   form  $-V \sum_{\langle i,j \rangle} n_i n_j$ , with  $n_i$  denoting the electron number operator at site  $i$ ,
   nodal liquids are discussed. We use the spin-charge separation ansatz as applied to
   the nodes of a d-wave superconducting ***gap***. Such a situation may be of
   relevance to the physics of high-temperature superconductivity. We point out the
   possibility of existence of certain points in the parameter space of the model
   characterized by dynamical supersymmetries between the spinon and holon degrees of
   freedom, which are quite different from the symmetries in conventional supersymmetric
   t-J models. Such symmetries pertain to the continuum effective-field theory of the
   nodal liquid, and one's hope is that the ancestor lattice model may differ from the
   continuum theory only by renormalization-group irrelevant operators in the infrared.
   We give plausible arguments that nodal liquids at such supersymmetric points are
   characterized by superconductivity of Kosterlitz-Thouless type. The fact that quantum
   fluctuations around such points can be studied in a controlled way, probably makes
   such systems of special importance for an eventual nonperturbative understanding of
   the complex phase diagram of associated high-temperature superconducting materials.
CT HIGH-TEMPERATURE SUPERCONDUCTORS; PHASE DIAGRAMS; SUPERCONDUCTING ENERGY
   ***GAP*** ; T-J MODEL
ST extended t-J models; nodal liquids; dynamical supersymmetry; intersite Coulomb
   interactions; ***superconducting gap*** ; high-temperature superconductivity; holon
   degrees of freedom; spin-on degrees of freedom; continuum effective-field theory;
   renormalization-group; Kosterlitz-Thouless superconductivity; quantum fluctuations;
   complex phase diagram
ET J; In; V
```

**Searching Co (cobalt), but not CO (carbon monoxide):**

```
=> S CO/ET NOT C*O/ET
      101729 CO/ET
      68785 C*O/ET
L3    57580 CO/ET NOT C*O/ET

=> D TI ET 3

L3    ANSWER 3 OF 57580 INSPEC COPYRIGHT 2000 IEE
TI    Co-depositi on of Au-Sn eutectic solder using pulsed current
      electroplating.
ET    ***Co*** ; Au*Sn; Au sy 2; sy 2; Sn sy 2; Au-Sn; Au; Sn; In*P; InP; In
      cp; cp; P cp; Au*Cl*K; Au sy 3; sy 3; Cl sy 3; K sy 3; KAuCl 4; K cp; Au
      cp; Cl cp; Cl *H*O*Sn; SnCl 2; Sn cp; 2H2O; H cp; O cp; SnCl 2-2H2O; AuSn;
      H2O; SnCl 2-H2O; KAuCl ; Cl ; SnCl 2H2O; H; O; In; P
```

**2. In case of molecular formulas, the formula itself, the elements in Hill System Order (see above) and additionally each element with the addition cp (compound) are indexed.**

$\text{NH}_4(\text{Cd}(\text{HCOO})_3) \rightarrow \text{NH}_4(\text{Cd}(\text{HCOO})_3)$ ; C\*H\*Cd\*N\*O; C cp; H cp; Cd cp; N cp; Ocp;cp

```
=> E NH4(CD/ET
E1    1 NH4(C4H5O5). H2O/ET
E2    1 NH4(C6H5COO)/ET
E3    0 --> NH4(CD/ET
E4    1 NH4(CH2)6/ET
E5    1 NH4(CH3)2PO4/ET
E6    1 NH4(CH3COO)/ET
E7    1 NH4(CN3H6)2(UO2(C2O4)2)/ET
E8    1 NH4(CO(OX)2(NH3)2). H2O/ET
E9    3 NH4(EU/ET
E10   3 NH4(FE/ET
E11   1 NH4(FE (THPU) (THSA))/ET
E12   1 NH4(FE, AL)/ET

=> S E1
L4    1 "NH4(C4H5O5). H2O" /ET

=> D TRIAL

L4    ANSWER 1 OF 1 INSPEC COPYRIGHT 2000 IEE
TI    Di electric and pyroelectric properties of ammoni um hydrogen-DL-mal ate
      monohydrate, NH4(C4H5O5). H2O.
CC    A7720 Permi tti vi ty; A7770 Pyroelectric and electrocal oric effects
CT    CRYSTAL FIELD INTERACTI ONS; DIELECTRIC PROPERTI ES OF LI QUI DS AND
      SOLUTI ONS; INDO CALCULATI ONS; ORGANI C COMPOUNDS; PERMI TTI VI TY;
      PYROELECTRI CI TY
ST    di electric properties; AC pl ane; SCEF cal cul ati ons; di electric constant;
      pyroelectric properties; ammoni um hydrogen-DL-mal ate monohydrate;
      temperature; crystallographi c di recti on; di electric tensor; pyroelectric
      coefficient; INDO procedure; crystal fi eld effects; charge di stri buti on;
      di pole moment; 100 K
PHP   temperature 1.0E+02 K
ET    C*H*N*O; ***NH4(C4H5O5). H2O*** ; N cp; cp; H cp; C cp; O cp;
      NH4(OOCCHOHCH2COOH). H2O; NH4(+)((-)OOCCHOHCH2COOH). H2O; C
```

**3. If a formula contains at least two metals or semimetals (as e.g. in an intermetallic compound) it is considered a SYSTEM. In this case, everything explained under 2. is valid, but in addition each element is indexed with sy (system). In case of material systems (e.g. alloys) characterized by hyphen between the elements, only sy together with the number of elements is indexed.**

$(\text{Al}_x\text{Ga}_{1-x})_{0.48}\text{In}_{0.52}\text{As} \rightarrow (\text{Al}_x\text{Ga}_{1-x})_{0.48}\text{In}_{0.52}\text{As}$ ; Al\*As\*Ga\*In;  
 Al sy 4; sy 4; As sy 4; Ga sy 4; In sy 4;  
 Al cp; cp; Ga cp; As cp; In cp

Al-Zn-Mg ----> Al-Zn-Mg; Al\*Mg\*Zn; Al sy 3; sy 3; Mg sy 3; Zn sy 3

```

=> S ALXGA/ET
L5      11 ALXGA/ET

=> E ALXGA/ET
E1      1      ALXFGA1-XAS/ET
E2      1      ALXG/ET
E3      11 --> ALXGA/ET
E4      5      ALXGA(1-X/ET
E5      1      ALXGA(1-X)/ET
E6      21     ALXGA(1-X)AS/ET
E7      1      ALXGA(1-X)AS-ALYGA(1-Y)AS/ET
E8      2      ALXGA(1-X)N/ET
E9      1      ALXGA(1-Y)AS/ET
E10     6      ALXGA-XAS/ET
E11     1      ALXGA-XAS-GAAS/ET
E12     1      ALXGA. /ET

=> S E7
L6      1 "ALXGA(1-X)AS-ALYGA(1-Y)AS" /ET

=> D TI ET

L6      ANSWER 1 OF 1  INSPEC  COPYRIGHT 2000 IEE
TI      Single-pass gain measurements on optically pumped Al xGa(1-x)As-Al yGa(1-
y)As double-heterojunction laser structures at room temperature.
ET      Al *As*Ga; Al sy 3; sy 3; As sy 3; Ga sy 3; Al xGa(1-x)As; Al cp; cp; Ga cp;
As cp; Al yGa(1-y)As; ***Al xGa(1-x)As-Al yGa(1-y)As*** ; As*Ga; As sy 2;
sy 2; Ga sy 2; GaAs; V

```

```

=> S AL*MG*ZN/ET
L7      1551 AL*MG*ZN/ET

=> D TRI AL

L7      ANSWER 1 OF 1551  INSPEC  COPYRIGHT 2000 IEE
TI      Refurbishment of aluminum alloys by laser cladding.
CC      A8160B Surface treatment and degradation of metals and alloys; A4262A
Laser materials processing; B4360B Laser materials processing; B0530
Metals and alloys (engineering materials science)
CT      ALUMINIUM ALLOYS; CLADDING TECHNIQUES; CORROSION RESISTANCE; FRACTURE
TOUGHNESS; LASER BEAM WELDING; LASER MATERIALS PROCESSING; MAINTENANCE
ENGIN EERING; MICROHARDNESS; OPTICAL MICROSCOPY; TENSILE STRENGTH
ST      alumi ni um alloy refurbishment; laser cladding; heat treatable components;
high value components; manufactured defects; alloy 6061-T6; alloy
7075-T651; optimum processing parameters; optical microscopy;
microhardness testing; mechanical testing; fracture analysis; corrosion
testing; laser beam welding; tensile strength; 3 kW; Al -Mg-Si; Al -Zn-Mg;
YAG: Nd; YAl 5012: Nd
CHI     Al sur, Al ss; Al MgSi sur, Al sur, Mg sur, Si sur, Al MgSi ss, Al ss, Mg
ss, Si ss; Al ZnMg sur, Al sur, Mg sur, Zn sur, Al ZnMg ss, Al ss, Mg ss, Zn
ss; YAl 5012: Nd ss, YAl 5012 ss, Al 5012 ss, Al 5 ss, 012 ss, Al ss, Nd ss, 0
ss, Y ss, Nd el, Nd dop
PHP     power 3.0E+03 W
ET      Nd; T; Al *Mg*Si; Al sy 3; sy 3; Mg sy 3; Si sy 3; Al -Mg-Si;
***Al *Mg*Zn*** ; Zn sy 3; Al -Zn-Mg; Al *O*Y; O sy 3; Y sy 3; YAl 50; Y cp;
cp; Al cp; O cp; Al; Al MgSi; Mg cp; Si cp; Mg; Si; Al ZnMg; Zn cp; Zn;
Al *O; Al 50; 0; Y

```

#### 4. Furthermore the following symbols are recognized and searchable:

- doping:  
Si:P ----> Si:P; P doping; doped materials; P\*Si; Si
- the symbols for elementary particles or phases etc. containing sub- or superscripts like +, -, or 0:  
SIGMA` ----> SIGMA-; SIGMA`
- positive (ip) or negative (in) ions:  
Be<sup>2+</sup> ----> Be2+; Be ip 2; Be; ip 2

- isotopes (is):  
 $^{54,56}\text{Fe} \rightarrow 54,56\text{Fe}; 54\text{Fe}; 56\text{Fe}; \text{Fe is}; \text{is}$

```
=> E BE IP/ET
E1      66      BE IN 1/ET
E2       2      BE IN 2/ET
E3       0 --> BE IP/ET
E4       1      BE IP 0/ET
E5      441     BE IP 1/ET
E6      270     BE IP 2/ET
E7       54     BE IP 3/ET
E8       53     BE IP 4/ET
E9        1     BE IP 5/ET
E10     5179    BE IS/ET
E11      1      BE KALPHA/ET
E12      1      BE SY 10/ET
```

=> S E2

```
L9      2 "BE IN 2"/ET

=> D TRIAL

L9      ANSWER 1 OF 2  INSPEC  COPYRIGHT 2000 IEE
TI      Direct determination of second-order density matrix using density
equation: Open-shell system and excited state.
CC      A3120 Specific calculations and results for atoms and molecules; A3150
Excited states of atoms and molecules
CT      ATOMIC STRUCTURE; EXCITED STATES; MOLECULAR ELECTRONIC STATES
ST      second-order density matrix; density equation; open-shell system; excited
state; spin-dependent density matrix; density matrices; closed-shell
system; Be(3S); Be-(2S); B+(3S); B(2S); C2+(3S); C+(2S); N3+(3S); N2+(2S);
Be; Be2-; B+; B-; C2+; N3+; H2O; HF; transition energies; spin densities;
spin-independent density matrix; N-fermion systems; operators; quantum
mechanics; B; C; N
CHI     Be el; B el; C el; N el; H2O bin, H2 bin, H bin, O bin; HF bin, F bin, H
bin
ET      Be; Be2-; ***Be in 2*** ; in 2; B; B+; B ip 1; ip 1; B-; B in 1; in 1;
C; C2+; C ip 2; ip 2; N; N3+; N ip 3; ip 3; H*O; H2O; H cp; cp; O cp; F*H;
HF; F cp; H; O
```

All formulas can be searched with special characters, but sometimes use of quotation marks in search statements is necessary. It is therefore recommended to use always quotation marks, as in the following example, when special characters (with the exception of '\*' and '-') are used.

```
=> S "54,56FE(N,P)54,56MN"/ET
L10     3 "54,56FE(N,P)54,56MN"/ET

=> D TRIAL

L10     ANSWER 1 OF 3  INSPEC  COPYRIGHT 2000 IEE
TI      The 54,56Fe(n,p)54,56Mn reactions at En=97 MeV.
CC      A2540F Inelastic neutron scattering and (n, p) reactions; A2740 39 <or= A
<or= 58; A9810 Stellar dynamics; A9530C Elementary particle and nuclear
processes; A9760B Supernovae; A2410F Plane- and distorted-wave Born
approximations; A2160J Hartree-Fock and random-phase approximations;
A2160C Shell model
CT      NEUTRON-NUCLEUS REACTIONS; NUCLEAR REACTION AND SCATTERING THEORY; NUCLEAR
SHELL MODEL; NUCLEI WITH MASS NUMBER 39 TO 58; RPA CALCULATIONS; STELLAR
DYNAMICS; SUPERNOVAE
ST      54Fe(n,p)54Mn; 56Fe(n,p)56Mn; DWBA; double-differential cross sections;
star dynamics; angular distributions; distorted-wave Born approximation;
Gamow-Teller strength; shell-model calculations; supernova explosions;
electron-capture rates; 1f2p-shell nuclei; L=1 strength; broad
distributions; random-phase approximation
ET      Fe(n,p)Mn; ***54,56Fe(n,p)54,56Mn*** ; 54,56Fe t; n r; n p; 54,56Mn f;
54,56Mn; is; Fe is; 56Fe; 54Fe; Mn is; 56Mn; 54Mn; Fe(n,p); 54,56Fe(n,p);
Fe; 54Fe(n,p)54Mn; 54Fe t; 54Mn f; 56Fe(n,p)56Mn; 56Fe t; 56Mn f
```

=> S 24-26MG/ET

L11 3 24-26MG/ET

=> D TRIAL

L11 ANSWER 1 OF 3 INSPEC COPYRIGHT 2000 IEE

TI Excitation of two nucleons into the continuum as a doorway process for bound-pion absorption by nuclei.

CC A2410 Nuclear reaction and scattering models and methods; A2580 Meson- and hyperon-induced reactions and scattering; A3610G Mesonic atoms and molecules, hyperonic atoms and molecules

CT MESONIC ATOMS; MESON ABSORPTION; NUCLEAR REACTION AND SCATTERING THEORY; PION-NUCLEUS REACTIONS

ST level width; pionic atoms; two nucleon excitation; P absorption; bound-pion absorption; 12C; 14N; O; 19F; 20Ne; 23Na; Mg; 27Al; 28Si; 31P; 32S; 35Cl; 39K; 40Ar; Ca; Ti; 51V; 52Cr; 209Bi; nuclear self-consistent theory; doorway process; S absorption

ET C; 12C; is; C is; N; 14N; N is; O; 16-18O; O is; 18O; 17O; 16O; F; 19F; F is; Ne; 20Ne; Ne is; Na; 23Na; Na is; Mg; \*\*\*24-26Mg\*\*\* ; Mg is; 26Mg; 25Mg; 24Mg; Al; 27Al; Al is; Si; 28Si; Si is; P; 31P; P is; S; 32S; S is; Cl; 35Cl; Cl is; K; 39K; K is; Ar; 40Ar; Ar is; Ca; 40-48Ca; Ca is; 48Ca; 47Ca; 46Ca; 45Ca; 44Ca; 43Ca; 42Ca; 41Ca; 40Ca; Ti; 46-50Ti; Ti is; 50Ti; 49Ti; 48Ti; 47Ti; 46Ti; V; 51V; V is; Cr; 52Cr; Cr is; Bi; 209Bi; Bi is

=> S "PI+"/ET

L12 92 "PI+"/ET

=> D TRIAL 2

L12 ANSWER 2 OF 92 INSPEC COPYRIGHT 2000 FIZ KARLSRUHE

TI D\* production in deep inelastic scattering at HERA.

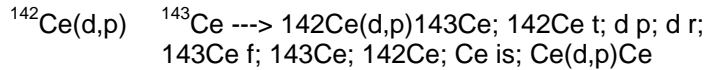
CC A1360H Total and inclusive cross sections; A1340F Electromagnetic form factors; electric and magnetic moments; structure functions; A1420E Protons; A0130Q Reports, dissertations, theses

CT DEEP INELASTIC SCATTERING; ELECTRON-PROTON INTERACTIONS; ELEMENTARY PARTICLE INCLUSIVE INTERACTIONS; HADRON ELECTROPRODUCTION; MESON PRODUCTION; PROTONS; STRUCTURE FUNCTIONS

ST positron+proton producing D\*++X; positron+proton producing D\*+X; DIS; deep inelastic scattering; HERA ZEUS detector; D\*+ decay into D0+pion+; D0 decay into kaon+pion+; inclusive D\* production cross section; differential cross sections; transverse momentum dependence; pseudorapidity dependence; energy dependence; momentum transfer dependence; next to leading order QCD; quantum chromodynamics; photon gluon fusion; extrapolation; full kinematic region; charm contribution; proton structure function; protons; Bjorken x; D\*- decay into antiD0+pion-; antiD0 decay into kaon+pion-; total cross section

ET D; D0; K; K-; pi; \*\*\*pi+\*\*\* ; W

**5. In nuclear reactions, the target nucleus is designated by t, the incident particle is designated by r and the final nucleus by f.**



Searching for deuterium reactions:

```
=> S D R/ET
L13      7297 D R/ET

=> D TI ET 1-5

L13 ANSWER 1 OF 7297 INSPEC COPYRIGHT 2000 IEE
TI Low energy deuteron-induced reactions on 27Al and 56Fe.
ET Al; 27Al; is; Al is; Fe; 56Fe; Fe is; (d,p); ***d r*** ; d p; (d, alpha); d alpha ;
(d,n); d n; T; Al (d,d); 27Al (d,d); 27Al t; d d; Al (d,d'); 27Al (d,d'); d d'; Fe(d,d);
56Fe(d,d); 56Fe t; Fe(d,d'); 56Fe(d,d'); Al (d,p); 27Al (d,p); Al (d, alpha );
7Al (d, alpha ); Al (d,n); 27Al (d,n); Fe(d,p); 56Fe(d,p); Fe(d, alpha ); 56Fe(d, alpha );
Fe(d,n); 56Fe(d,n)

L13 ANSWER 2 OF 7297 INSPEC COPYRIGHT 2000 IEE
TI R-matrix fits involving levels of 8Be.
ET Be; 8Be; is; Be is; He; 4He; He is; Li; 7Li; Li is; 7Be; Li (p, alpha )He;
7Li (p, alpha )4He; 7Li t; p r; p alpha ; 4He f; Li (p, alpha )He: S; 7Li (p, alpha )4He: S;
4He: S f; 4He: S; S doping; doped materials; Li (d, alpha alpha ); 7Li (d, alpha alpha );
***d r*** ; d alpha alpha ; Li (p, gamma 0)Be; 7Li (p, gamma 0)8Be; p gamma 0; 8Be f;
Li (d, alpha alpha n); 7Li (d, alpha alpha n); d alpha alpha n

L13 ANSWER 3 OF 7297 INSPEC COPYRIGHT 2000 FIZ KARLSRUHE
TI Pion production in the d4He to 6Li * pi 0 reaction near threshold.
ET He; 4He; is; He is; Li; 6Li; Li is; 3He; He(d, pion); 4He(d, pion0); 4He t;
***d r*** ; d pion0; H(p, pion)He; H(p, pion0)3He; H t; p r; p pion0; 3He f

L13 ANSWER 4 OF 7297 INSPEC COPYRIGHT 2000 FIZ KARLSRUHE
TI Investigation of 50Cr(d,n)51Mn and natCr(p,X)51Mn processes with respect
to the production of the positron emitter 51Mn.
ET Cr(d,n)Mn; 50Cr(d,n)51Mn; 50Cr t; ***d r*** ; d n; 51Mn f; 51Mn; is; Cr is; 50Cr;
Mn is; Cr(p,X)Mn; Cr(p,X)51Mn; Cr t; p r; p X; Mn; Cr; Cr(d,2n)Mn; 50Cr(d,2n)50mMn;
d 2n; 50mMn f; 50mMn; 50Mn; Cr(d,t)Cr; 50Cr(d,t)49Cr; d t; 49Cr f; 49Cr; Cr(d,p)Cr;
50Cr(d,p)51Cr; d p; 51Cr f; 51Cr; Cr(d, alpha )V; 50Cr(d, alpha )48V; d alpha ; 48V f;
48V; V is; Cr(d,2p)V; 52Cr(d,2p)52V; 52Cr t; d 2p; 52V f; 52V; 52Cr; Cr(p,X)52Mn;
52Mn f; 52Mn; Cr(p,X)52mMn; 52mMn f; 52mMn; Cr(p,X)54Mn; 54Mn f; 54Mn; Cr(p,X)Cr;
Cr(p,X)48Cr; 48Cr f; 48Cr; Cr(p,X)49Cr; Cr(p,X)51Cr; Cr(p,X)V; Cr(p,X)48V; Cr(p,X)Ti;
Cr(p,X)45Ti; 45Ti f; 45Ti; Ti is; 52mgMn; 52gMn; Cr(p,x)Mn; Cr(p,x)51Mn; p x; Cr(d,n);
50Cr(d,n); Cr(p,X); Cr(d,2n); 50Cr(d,2n); Cr(d,t); 50Cr(d,t); Cr(d,p); 50Cr(d,p);
Cr(d, alpha ); 50Cr(d, alpha ); d alpha ; Cr(d,2p); 52Cr(d,2p)

L13 ANSWER 5 OF 7297 INSPEC COPYRIGHT 2000 IEE
TI Ab initio analysis of C-H and C-C stretching intensities in Raman spectra
of hydrocarbons.
ET C*H; C-H; C-C; C; F*H; HF; H cp; cp; F cp; (d,p); ***d r*** ; d p
```

## Appendix: Examples for the Field /ET

In the SEARCH command use ! instead of (), []. Quotation marks may also be used after the search term.

<b>Material Description</b>		
<b>In title or abstract of documentation unit on magnetic tape</b>	<b>In the online citation (first line) and in the field /ET (all lines)</b>	<b>Remarks</b>
Ucl <sub>5</sub>	Ucl5 Cl*U U cp Cl cp	Compounds (CP)
NH <sub>4</sub> [Cd(HCOO) <sub>3</sub> ]	NH4[Cd(HCOO)3] C*H*Cd*N*O C cp H cp Cd cp N cp O cp cp	Compounds
<sup>22</sup> Na <sub>2</sub> S <sup>18</sup> O	22Na2S18O4 Na2SO4 Na*O*S 22Na Na is 18O O is Na cp O cp S cp cp	Isotopes (IS) Compounds
Si:P	Si:P P doping doped materials Si P*Si	Doped Materials
[CeCl <sub>4</sub> (NO <sub>3</sub> ) <sub>2</sub> ] <sup>2-</sup>	[CeCl4(NO3)2]2- [CeCl4(NO3)2] in 2 Ce*Cl*N*O in 2 Ce cp Cl cp N cp O cp cp	Ion Negative (IN)
Be <sup>2+</sup>	Be2+ Be ip 2 Be ip 2	Ion Positive (IP)
<sup>24-26</sup> Mg	24-26Mg 26Mg 25Mg 24Mg Mg is Mg is	Range of Isotopes

<b>Material Description</b>		
<b>In title or abstract of documentation unit on magnetic tape</b>	<b>In the online citation (first line) and in the field /ET (all line)</b>	<b>Remarks</b>
$\sigma$ -oder SIGMA-	SIGMA-SIGMA	Greek Letters (phases, particles)
$^{142}\text{Ce}(d,p)^{143}\text{CE}$	142Ce(d,p)143Ce 142Ce t d p d r 143Ce f 143Ce CE is Ce(d,p)Ce	Nuclear Reactions
In-Bi	In-Bi Bi*In Bi sy 2 In sy 2 Bi *) In sy 2	Systems/Alloys at least 2 metals/ semicond. (SY), figure gives number of elements
$\text{K}_3\text{xFe}_x\text{W}_{1-x}\text{O}_6$	$\text{K}_3\text{xFe}_x\text{W}_{1-x}\text{O}_6$ Fe*K*O*W Fe sy 4 K sy 4 O sy 4 W sy 4 sy 4	Systems
AlCuMg <sub>2</sub>	AlCuMg2 Al*Cu*Mg Al sy 3 Cu sy 3 Mg sy 3 sy 3 Al cp Cu cp Mg cp	Intermetallic Compounds, indexed as Systems too
$\text{NH}_4\text{Sc}(\text{WO}_4)_2 \cdot 4.5\text{H}_2\text{O}$	$\text{NH}_4\text{Sc}(\text{WO}_4)_2 \cdot 4.5\text{H}_2\text{O}$ H*N*O*Sc*W H sy 5 N sy 5 O sy 5 Sc sy 5 W sy 5 sy 5 H cp N cp O cp Sc cp W cp cp	Compound with two or more metals/ semicond. indexed as SY and CP
KhGNM	KhGNM CrMnNiMo Cr*Mn*Mo*Ni Cr sy 4 Mn sy 4 Mo sy 4 Ni sy 4 sy 4	Russian Steels First example only in TI and AB

\*) When in the original documentation unit the material description contains a hyphen, the pure elements are given in the ET field, too. Therefore, pure elements should be searched in the CT field.